

1. Scope :

This specification applies to silicon switching diode chips,
Device No. SD-0013.

2. Structure :

- 2-1. Mesa type.
- 2-2. Electrodes:
P (Anode) Side: Aluminum alloy.
N (Cathode) Side: Gold alloy.

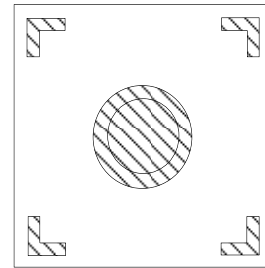
3. Size :

- 3-1. Chip size: 13 mils x 13 mils (0.330 mm x 0.330 mm).
- 3-2. Chip Thickness: 7.5 mils ± 1.5 mils (0.191 mm ± 0.038 mm).
- 3-3. Pattern drawing: Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F =10mA Ee=0mW/cm ²	0.77	0.82	0.87	V
Reverse Current	I _R	V _R =80V Ee=0mW/cm ²		0.5	1.0	μA
Reverse Breakdown Voltage	V _{(BV)R}	I _R =5μA Ee=0mW/cm ²	100			V

PATTERN DRAWING
UNIT: mil



5. Packing and labeling :

5-1. Packing :

Two types can be chosen:

PSA :Sheet type

Each pellet is mounted on an adhesive sheet
With wire-bonded electrode side up.

NS :Sheet type

Each pellet is mounted on an adhesive sheet
With back electrode side up.

5-2. Labeling :

Each lot has a label sheet, writing type, lot no,
PCS,avg. , and quantity of good chips.

